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Method Of Growing Semipolar Gallium Nitride Film



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MEGA-TREND

- Future of Consumer Electronics
- Chemicals and Materials

TECHNOLOGY READINESS LEVEL (TRL)

- TRL 3

PATENT/ GRANTED NUMBER

- UI 2017704972

▶ TECHNOLOGY OVERVIEW

A method of growing semipolar GaN on m-plane sapphire substrate using metalorganic chemical vapor deposition (MOCVD) is described. A suitable m-plane Al₂O₃ is used as substrate. Nitridation of substrate is performed at growth temperature with gaseous H₂ and NH₃ flow. After a desired time has elapsed, growth of planar m-plane GaN layer on the substrate is performed with gaseous (Ga(CH₃)₃), H₂ and NH₃ flow. Semipolar m-plane GaN is grown on the substrate. The surface morphology of semipolar GaN has improved as captured by atomic force microscope and scanning electron microscope.

CONTACT US!

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